



RESPONSE UNDER 37 CFR 1.116
EXPEDITED PROCEDURE
EXAMINING GROUP 2818

PATENT APPLICATION
Do. No. 5484-093

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Byeong-Hoon LEE, et al.

Serial No. 09/997,080

Examiner: Phan, Trong Q

Confirmation No. 6095

Filed: November 28, 2001

Group Art Unit: 2818

For: NONVOLATILE SEMICONDUCTOR MEMORY DEVICE

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Assistant Commissioner for Patents
Washington, D.C. 20231

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M. Brauns on
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AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR 1.116

Responsive to the Final Office Action, dated November 14, 2002, please amend the application as follows.

IN THE CLAIMS

A full set of pending claims is reproduced below for the Examiner's convenience.

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1. A nonvolatile semiconductor memory device comprising:
a plurality of sectors;
each sector comprising memory cell transistors arranged in a cell array block and decoder transistors in a column decoder block;
wherein the transistors in the cell array block and column decoder block in each sector share a common bulk region; and
wherein said semiconductor memory device is configured to electrically erase all the memory cell transistors in a sector together.
2. A nonvolatile semiconductor memory device according to claim 1, wherein the semiconductor memory device is a NOR-type memory device.

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